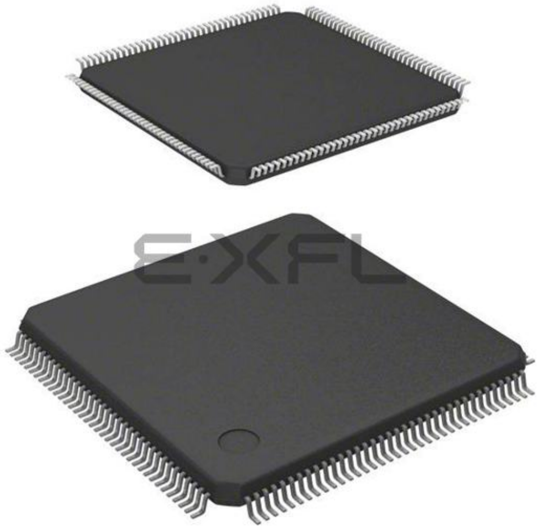

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	114
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f427zit6

3.4 Embedded Flash memory

The devices embed a Flash memory of up to 2 Mbytes available for storing programs and data.

3.5 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a software signature during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.6 Embedded SRAM

All devices embed:

- Up to 256Kbytes of system SRAM including 64 Kbytes of CCM (core coupled memory) data RAM

  RAM memory is accessed (read/write) at CPU clock speed with 0 wait states.
- 4 Kbytes of backup SRAM

  This area is accessible only from the CPU. Its content is protected against possible unwanted write accesses, and is retained in Standby or V_{BAT} mode.

3.7 Multi-AHB bus matrix

The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs, Ethernet, USB HS, LCD-TFT, and DMA2D) and the slaves (Flash memory, RAM, FMC, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high-speed peripherals work simultaneously.

3.22.4 Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 32 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes.

3.22.5 Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.22.6 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard downcounter. It features:

- A 24-bit downcounter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source.

3.23 Inter-integrated circuit interface (I^2C)

Up to three I^2C bus interfaces can operate in multimaster and slave modes. They can support the standard (up to 100 KHz), and fast (up to 400 KHz) modes. They support the 7/10-bit addressing mode and the 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SMBus 2.0/PMBus.

The devices also include programmable analog and digital noise filters (see *Table 7*).

Table 7. Comparison of I2C analog and digital filters

	Analog filter	Digital filter
Pulse width of suppressed spikes	≥ 50 ns	Programmable length from 1 to 15 I2C peripheral clocks

3.24 Universal synchronous/asynchronous receiver transmitters (USART)

The devices embed four universal synchronous/asynchronous receiver transmitters (USART1, USART2, USART3 and USART6) and four universal asynchronous receiver transmitters (UART4, UART5, UART7, and UART8).

These six interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability. The USART1 and USART6 interfaces are able to

3.39 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 1.7 V and 3.6 V. The temperature sensor is internally connected to the same input channel as V_{BAT}, ADC1_IN18, which is used to convert the sensor output voltage into a digital value. When the temperature sensor and V_{BAT} conversion are enabled at the same time, only V_{BAT} conversion is performed.

As the offset of the temperature sensor varies from chip to chip due to process variation, the internal temperature sensor is mainly suitable for applications that detect temperature changes instead of absolute temperatures. If an accurate temperature reading is needed, then an external temperature sensor part should be used.

3.40 Digital-to-analog converter (DAC)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs.

This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- 8-bit or 10-bit monotonic output
- left or right data alignment in 12-bit mode
- synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channel independent or simultaneous conversions
- DMA capability for each channel
- external triggers for conversion
- input voltage reference V_{REF+}

Eight DAC trigger inputs are used in the device. The DAC channels are triggered through the timer update outputs that are also connected to different DMA streams.

3.41 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

Debug is performed using 2 pins only instead of 5 required by the JTAG (JTAG pins could be re-use as GPIO with alternate function): the JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number								Pin name (function after reset)(1)	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA169	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
-	10	F2	E2	16	F11	16	D2	PF0	I/O	FT	-	I2C2_SDA, FMC_A0, EVENTOUT	-
-	11	F3	H3	17	E9	17	E2	PF1	I/O	FT	-	I2C2_SCL, FMC_A1, EVENTOUT	-
-	12	G5	H2	18	F10	18	G2	PF2	I/O	FT	-	I2C2_SMBA, FMC_A2, EVENTOUT	-
-	-	-	-	-	-	19	E3	PI12	I/O	FT	-	LCD_HSYNC, EVENTOUT	-
-	-	-	-	-	-	20	G3	PI13	I/O	FT	-	LCD_VSYNC, EVENTOUT	-
-	-	-	-	-	-	21	H3	PI14	I/O	FT		LCD_CLK, EVENTOUT	-
-	13	G4	J2	19	G11	22	H2	PF3	I/O	FT	(5)	FMC_A3, EVENTOUT	ADC3_IN9
-	14	G3	J3	20	F9	23	J2	PF4	I/O	FT	(5)	FMC_A4, EVENTOUT	ADC3_IN14
-	15	H3	K3	21	F8	24	K3	PF5	I/O	FT	(5)	FMC_A5, EVENTOUT	ADC3_IN15
10	16	G7	G2	22	H7	25	H6	V_{SS}	S	-	-	-	-
11	17	G8	G3	23	-	26	H5	V_{DD}	S	-	-	-	-
-	18	NC (2)	K2	24	G10	27	K2	PF6	I/O	FT	(5)	TIM10_CH1, SPI5_NSS, SAI1_SD_B, UART7_Rx, FMC_NIORD, EVENTOUT	ADC3_IN4
-	19	NC (2)	K1	25	F7	28	K1	PF7	I/O	FT	(5)	TIM11_CH1, SPI5_SCK, SAI1_MCLK_B, UART7_Tx, FMC_NREG, EVENTOUT	ADC3_IN5
-	20	NC (2)	L3	26	H11	29	L3	PF8	I/O	FT	(5)	SPI5_MISO, SAI1_SCK_B, TIM13_CH1, FMC_NIOWR, EVENTOUT	ADC3_IN6

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number								Pin name (function after reset)(1)	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA169	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
82	115	C9	C12	143	C4	165	C12	PD1	I/O	FT	-	CAN1_TX, FMC_D3, EVENTOUT	-
83	116	B9	D12	144	A3	166	D12	PD2	I/O	FT	-	TIM3_ETR, UART5_RX, SDIO_CMD, DCMI_D11, EVENTOUT	-
84	117	A9	D11	145	B4	167	C11	PD3	I/O	FT	-	SPI2_SCK/I2S2_CK, USART2_CTS, FMC_CLK, DCMI_D5, LCD_G7, EVENTOUT	-
85	118	D8	D10	146	B5	168	D11	PD4	I/O	FT	-	USART2_RTS, FMC_NOE, EVENTOUT	-
86	119	C8	C11	147	A4	169	C10	PD5	I/O	FT	-	USART2_TX, FMC_NWE, EVENTOUT	-
-	120	-	D8	148	-	170	F8	V_{SS}	S		-	-	-
-	121	D6	C8	149	C5	171	E9	V_{DD}	S		-	-	-
87	122	B8	B11	150	F4	172	B11	PD6	I/O	FT	-	SPI3_MOSI/I2S3_SD, SAI1_SD_A, USART2_RX, FMC_NWAIT, DCMI_D10, LCD_B2, EVENTOUT	-
88	123	A8	A11	151	A5	173	A11	PD7	I/O	FT	-	USART2_CK, FMC_NE1/FMC_NCE2, EVENTOUT	-
-	-	-	-	-	-	174	B10	PJ12	I/O	FT	-	LCD_B0, EVENTOUT	-
-	-	-	-	-	-	175	B9	PJ13	I/O	FT	-	LCD_B1, EVENTOUT	-
-	-	-	-	-	-	176	C9	PJ14	I/O	FT	-	LCD_B2, EVENTOUT	-
-	-	-	-	-	-	177	D10	PJ15	I/O	FT	-	LCD_B3, EVENTOUT	-
-	124	NC (2)	C10	152	E5	178	D9	PG9	I/O	FT	-	USART6_RX, FMC_NE2/FMC_NCE3, DCMI_VSYNC(8), EVENTOUT	-

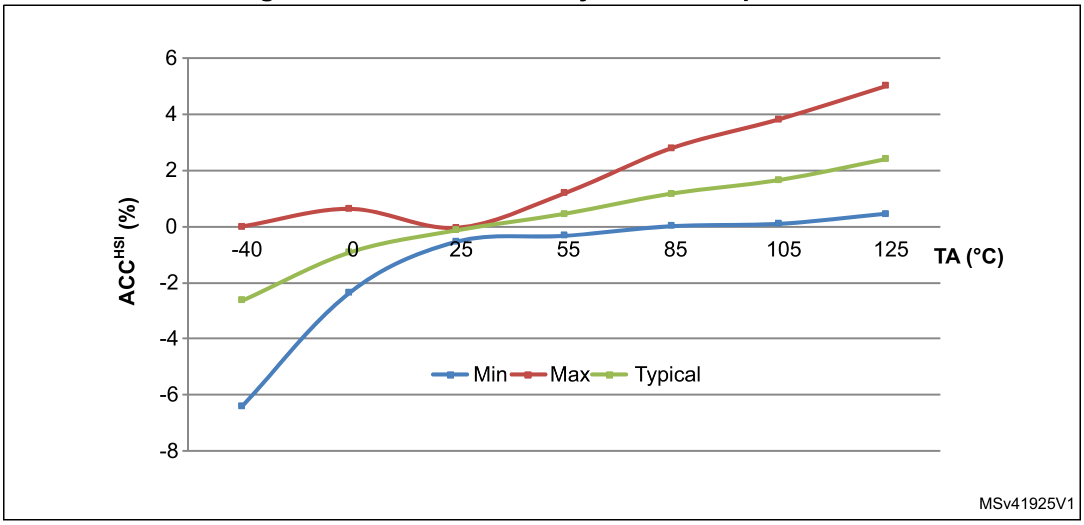
Table 12. STM32F427xx and STM32F429xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/ SAI1	SPI3/ USART1/ 2/3	USART6/ UART4/5/7 /8	CAN1/2/ TIM12/13/14 /LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS
Port H	PH7	-	-	-	-	I2C3_ SCL	SPI5_ MISO	-	-	-	-	-	ETH_MII_ RXD3	FMC_ SDCKE1	DCMI_ D9	-	-
Port H	PH8	-	-	-	-	I2C3_ SDA	-	-	-	-	-	-	-	FMC_D16	DCMI_ HSYNC	LCD_R2	EVEN TOUT
Port H	PH9	-	-	-	-	I2C3_ SMBA	-	-	-	-	TIM12_CH2	-	-	FMC_D17	DCMI_ D0	LCD_R3	EVEN TOUT
Port H	PH10	-	-	TIM5_ CH1	-	-	-	-	-	-	-	-	-	FMC_D18	DCMI_ D1	LCD_R4	EVEN TOUT
Port H	PH11	-	-	TIM5_ CH2	-	-	-	-	-	-	-	-	-	FMC_D19	DCMI_ D2	LCD_R5	EVEN TOUT
Port H	PH12	-	-	TIM5_ CH3	-	-	-	-	-	-	-	-	-	FMC_D20	DCMI_ D3	LCD_R6	EVEN TOUT
Port H	PH13	-	-	-	TIM8_ CH1N	-	-	-	-	-	CAN1_TX	-	-	FMC_D21	-	LCD_G2	EVEN TOUT
Port H	PH14	-	-	-	TIM8_ CH2N	-	-	-	-	-	-	-	-	FMC_D22	DCMI_ D4	LCD_G3	EVEN TOUT
Port H	PH15	-	-	-	TIM8_ CH3N	-	-	-	-	-	-	-	-	FMC_D23	DCMI_ D11	LCD_G4	EVEN TOUT
Port I	PI0	-	-	TIM5_ CH4	-	-	SPI2_ NSS/I2 S2_WS	-	-	-	-	-	-	FMC_D24	DCMI_ D13	LCD_G5	EVEN TOUT
Port I	PI1	-	-	-	-	-	SPI2_ SCK/I2 S2_CK	-	-	-	-	-	-	FMC_D25	DCMI_ D8	LCD_G6	EVEN TOUT
Port I	PI2	-	-	-	TIM8_ CH4	-	SPI2_ MISO	I2S2ext_ SD	-	-	-	-	-	FMC_D26	DCMI_ D9	LCD_G7	EVEN TOUT
Port I	PI3	-	-	-	TIM8_ ETR	-	SPI2_M OSI/I2S 2_SD							FMC_D27	DCMI_D 10		EVEN TOUT
Port I	PI4	-	-	-	TIM8_ BKIN	-	-	-	-	-	-	-	-	FMC_ NBL2	DCMI_D 5	LCD_B4	EVEN TOUT
Port I	PI5	-	-	-	TIM8_ CH1	-	-	-	-	-	-	-	-	FMC_ NBL3	DCMI_ VSYNC	LCD_B5	EVEN TOUT
Port I	PI6	-	-	-	TIM8_ CH2	-	-	-	-	-	-	-	-	FMC_D28	DCMI_ D6	LCD_B6	EVEN TOUT

Table 35. Peripheral current consumption (continued)

Peripheral		I_{DD}(Typ)(1)			Unit
		Scale 1	Scale 2	Scale 3	
AHB2 (up to 180 MHz)	OTG_FS	25.67	26.67	23.58	µA/MHz
	DCMI	3.72	3.40	3.00	
	RNG	2.28	2.36	2.17	
AHB3 (up to 180 MHz)	FMC	21.39	19.79	17.50	µA/MHz
Bus matrix(2)		14.06	13.19	11.75	µA/MHz
APB1 (up to 45 MHz)	TIM2	17.56	16.42	14.47	µA/MHz
	TIM3	14.22	13.36	11.80	
	TIM4	14.89	13.64	12.13	
	TIM5	17.33	16.42	14.47	
	TIM6	2.89	2.53	2.47	
	TIM7	3.11	2.81	2.47	
	TIM12	7.33	6.97	6.13	
	TIM13	4.89	4.47	4.13	
	TIM14	5.56	5.31	4.80	
	PWR	11.11	10.31	9.13	
	USART2	4.22	3.92	3.47	
	USART3	4.44	4.19	3.80	
	UART4	4.00	3.92	3.47	
	UART5	4.00	3.92	3.47	
	UART7	4.00	3.92	3.47	
	UART8	3.78	3.92	3.47	
	I2C1	4.00	3.92	3.47	
	I2C2	4.00	3.92	3.47	
	I2C3	4.00	3.92	3.47	
	SPI2(3)	3.11	3.08	2.80	
	SPI3(3)	3.56	3.36	3.13	
	I2S2	2.89	2.81	2.47	
	I2S3	3.33	3.08	2.80	
	CAN1	6.89	6.42	5.80	
	CAN2	6.67	6.14	5.47	
	DAC(4)	2.89	2.25	2.13	
	WWDG	0.89	0.86	0.80	

Figure 31. ACCHSI accuracy versus temperature



1. Guaranteed by characterization results.

Low-speed internal (LSI) RC oscillator

Table 42. LSI oscillator characteristics (1)

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}(2)	Frequency	17	32	47	kHz
$t_{su(LSI)}$(3)	LSI oscillator startup time	-	15	40	µs
$I_{DD(LSI)}$(3)	LSI oscillator power consumption	-	0.4	0.6	µA

1. V_{DD} = 3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by characterization results.
3. Guaranteed by design.

6.3.13 Memory characteristics

Flash memory

The characteristics are given at TA = –40 to 105 °C unless otherwise specified.

The devices are shipped to customers with the Flash memory erased.

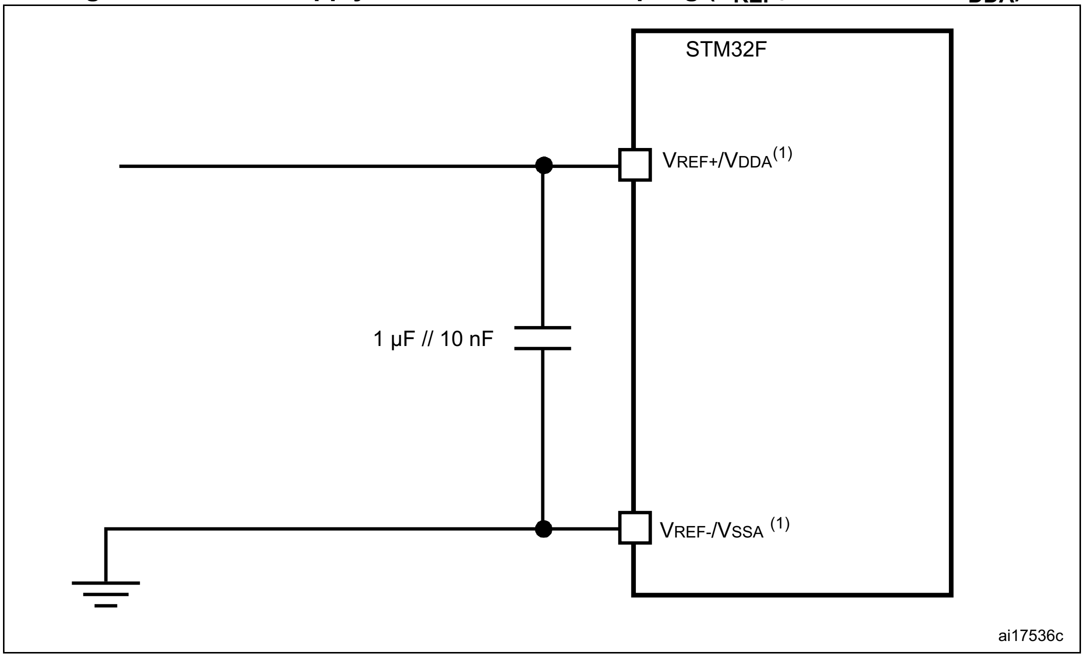
Table 47. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{DD}	Supply current	Write / Erase 8-bit mode, V_{DD} = 1.7 V	-	5	-	mA
		Write / Erase 16-bit mode, V_{DD} = 2.1 V	-	8	-	
		Write / Erase 32-bit mode, V_{DD} = 3.3 V	-	12	-	

Table 48. Flash memory programming

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	Word programming time	Program/erase parallelism (PSIZE) = x 8/16/32	-	16	100(2)	µs
$t_{ERASE16KB}$	Sector (16 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	400	800	ms
		Program/erase parallelism (PSIZE) = x 16	-	300	600	
		Program/erase parallelism (PSIZE) = x 32	-	250	500	
$t_{ERASE64KB}$	Sector (64 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	1200	2400	ms
		Program/erase parallelism (PSIZE) = x 16	-	700	1400	
		Program/erase parallelism (PSIZE) = x 32	-	550	1100	
$t_{ERASE128KB}$	Sector (128 KB) erase time	Program/erase parallelism (PSIZE) = x 8	-	2	4	s
		Program/erase parallelism (PSIZE) = x 16	-	1.3	2.6	
		Program/erase parallelism (PSIZE) = x 32	-	1	2	
t_{ME}	Mass erase time	Program/erase parallelism (PSIZE) = x 8	-	16	32	s
		Program/erase parallelism (PSIZE) = x 16	-	11	22	
		Program/erase parallelism (PSIZE) = x 32	-	8	16	

Figure 53. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are both available on UFBGA176. V_{REF+} is also available on LQFP100, LQFP144, and LQFP176. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA}.

6.3.22 Temperature sensor characteristics

Table 80. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L (1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	-	2.5		mV/°C
V_{25} (1)	Voltage at 25 °C	-	0.76		V
t_{START} (2)	Startup time	-	6	10	µs
T_{S_temp} (2)	ADC sampling time when reading the temperature (1 °C accuracy)	10	-	-	µs

1. Guaranteed by characterization results.
2. Guaranteed by design.

Table 81. Temperature sensor calibration values

Symbol	Parameter	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C, V_{DDA}= 3.3 V	0x1FFF 7A2C - 0x1FFF 7A2D
TS_CAL2	TS ADC raw data acquired at temperature of 110 °C, V_{DDA}= 3.3 V	0x1FFF 7A2E - 0x1FFF 7A2F

6.3.23 V_{BAT} monitoring characteristics

Table 82. V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Typ	Max	Unit
R	Resistor bridge for V_{BAT}	-	50	-	KΩ
Q	Ratio on V_{BAT} measurement	-	4	-	
Er(1)	Error on Q	–1	-	+1	%
T_{S_vbat}(2)(2)	ADC sampling time when reading the V_{BAT} 1 mV accuracy	5	-	-	µs

1. Guaranteed by design.
2. Shortest sampling time can be determined in the application by multiple iterations.

6.3.24 Reference voltage

The parameters given in *Table 83* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 17*.

Table 83. internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	–40 °C < T_A < +105 °C	1.18	1.21	1.24	V
$T_{S\_vrefint}$(1)	ADC sampling time when reading the internal reference voltage		10	-	-	µs
V_{RERINT_s}(2)	Internal reference voltage spread over the temperature range	V_{DD} = 3V ± 10mV	-	3	5	mV
T_{Coeff}(2)	Temperature coefficient		-	30	50	ppm/°C
t_{START}(2)	Startup time		-	6	10	µs

1. Shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design, not tested in production

Table 84. Internal reference voltage calibration values

Symbol	Parameter	Memory address
V_{REFIN_CAL}	Raw data acquired at temperature of 30 °C $_{VDDA}$ = 3.3 V	0x1FFF 7A2A - 0x1FFF 7A2B

6.3.25 DAC electrical characteristics

Table 85. DAC characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit	Comments
V_{DDA}	Analog supply voltage	-		1.7(1)	-	3.6	V	-
V_{REF+}	Reference supply voltage	-		1.7(1)	-	3.6	V	$V_{REF+} \leq V_{DDA}$
V_{SSA}	Ground	-		0	-	0	V	-
R_{LOAD}(2)	Resistive load	DAC output buffer ON	R_{LOAD} connected to V_{SSA}	5	-	-	kΩ	-
			R_{LOAD} connected to V_{DDA}	25			kΩ	-
R_O(2)	Impedance output with buffer OFF	-		-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and V_{SS} to have a 1% accuracy is 1.5 MΩ
C_{LOAD}(2)	Capacitive load	-		-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT min(2)	Lower DAC_OUT voltage with buffer ON	-		0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{REF+} = 3.6 V and (0x1C7) to (0xE38) at V_{REF+} = 1.7 V
DAC_OUT max(2)	Higher DAC_OUT voltage with buffer ON	-		-	-	V_{DDA} – 0.2	V	
DAC_OUT min(2)	Lower DAC_OUT voltage with buffer OFF	-		-	0.5	-	mV	It gives the maximum output excursion of the DAC.
DAC_OUT max(2)	Higher DAC_OUT voltage with buffer OFF	-		-	-	V_{REF+} – 1LSB	V	
I_{VREF+}(4)	DAC DC V_{REF} current consumption in quiescent mode (Standby mode)	-		-	170	240	µA	With no load, worst code (0x800) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs
		-		-	50	75	µA	With no load, worst code (0xF1C) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs

Table 90. Asynchronous multiplexed PSRAM/NOR read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK} - 1$	$3T_{HCLK}+0.5$	ns
$t_{v(NOE\_NE)}$	FMC_NEx low to FMC_NOE low	$2T_{HCLK} - 0.5$	$2T_{HCLK}$	ns
$t_{tw(NOE)}$	FMC_NOE low time	$T_{HCLK} - 1$	$T_{HCLK}+1$	ns
$t_{h(NE\_NOE)}$	FMC_NOE high to FMC_NE high hold time	1	-	ns
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	2	ns
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	0	2	ns
$t_{w(NADV)}$	FMC_NADV low time	$T_{HCLK} - 0.5$	$T_{HCLK}+0.5$	ns
$t_{h(AD\_NADV)}$	FMC_AD(address) valid hold time after FMC_NADV high)	0	-	ns
$t_{h(A\_NOE)}$	Address hold time after FMC_NOE high	$T_{HCLK} - 0.5$	-	ns
$t_{h(BL\_NOE)}$	FMC_BL time after FMC_NOE high	0	-	ns
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	2	ns
$t_{su(Data\_NE)}$	Data to FMC_NEx high setup time	$T_{HCLK}+1.5$	-	ns
$t_{su(Data\_NOE)}$	Data to FMC_NOE high setup time	$T_{HCLK}+1$	-	ns
$t_{h(Data\_NE)}$	Data hold time after FMC_NEx high	0	-	ns
$t_{h(Data\_NOE)}$	Data hold time after FMC_NOE high	0	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

Table 91. Asynchronous multiplexed PSRAM/NOR read-NWAIT timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK}+0.5$	$8T_{HCLK}+2$	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK} - 1$	$5T_{HCLK} +1.5$	ns
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK} +1.5$	-	ns
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}+1$		ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

Figure 58. Asynchronous multiplexed PSRAM/NOR write waveforms

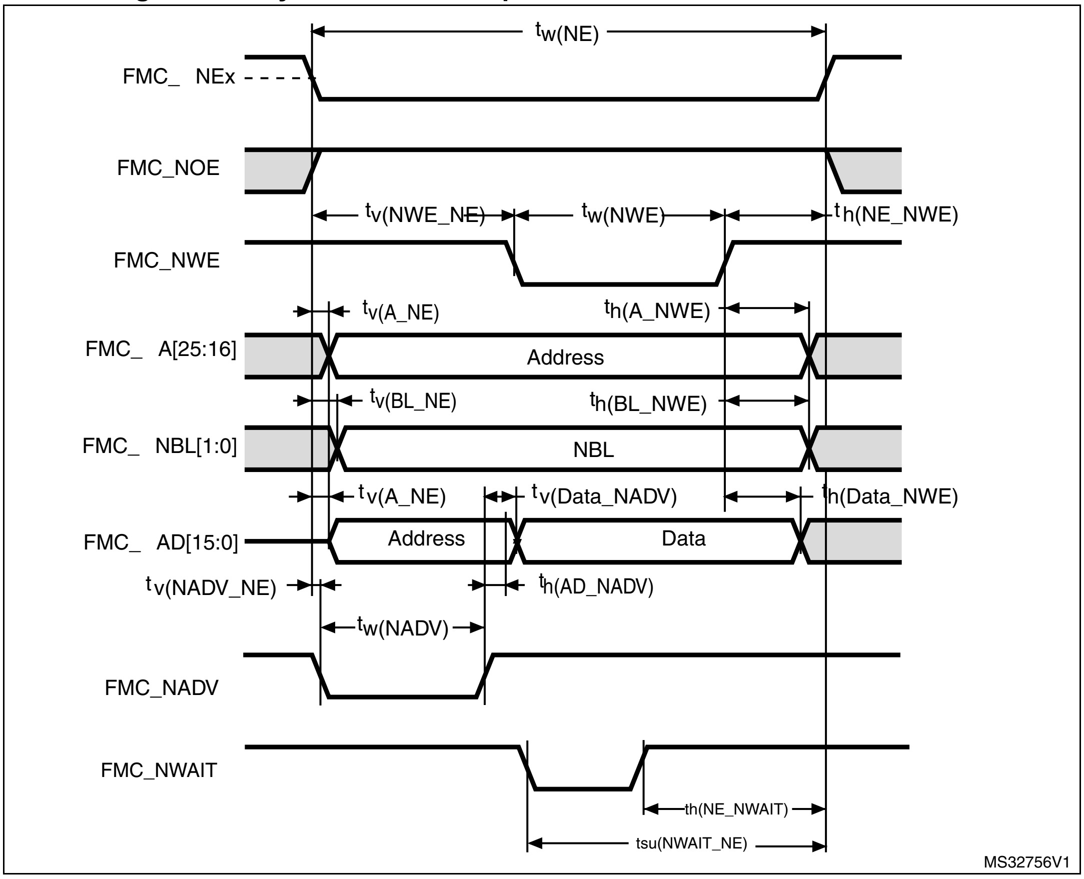


Table 92. Asynchronous multiplexed PSRAM/NOR write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$4T_{HCLK}$	$4T_{HCLK}+0.5$	ns
$t_{v(NWE\_NE)}$	FMC_NEx low to FMC_NWE low	$T_{HCLK} - 1$	$T_{HCLK}+0.5$	ns
$t_{w(NWE)}$	FMC_NWE low time	$2T_{HCLK}$	$2T_{HCLK}+0.5$	ns
$t_{h(NE\_NWE)}$	FMC_NWE high to FMC_NE high hold time	T_{HCLK}	-	ns
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0	ns
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	0.5	1	ns
$t_{w(NADV)}$	FMC_NADV low time	$T_{HCLK} - 0.5$	$T_{HCLK}+ 0.5$	ns
$t_{h(AD\_NADV)}$	FMC_AD(adress) valid hold time after FMC_NADV high)	$T_{HCLK} - 2$	-	ns
$t_{h(A\_NWE)}$	Address hold time after FMC_NWE high	T_{HCLK}	-	ns
$t_{h(BL\_NWE)}$	FMC_BL hold time after FMC_NWE high	$T_{HCLK} - 2$	-	ns
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	2	ns
$t_{v(Data\_NADV)}$	FMC_NADV high to Data valid	-	$T_{HCLK} +1.5$	ns
$t_{h(Data\_NWE)}$	Data hold time after FMC_NWE high	$T_{HCLK} +0.5$	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

Figure 69. NAND controller waveforms for read access

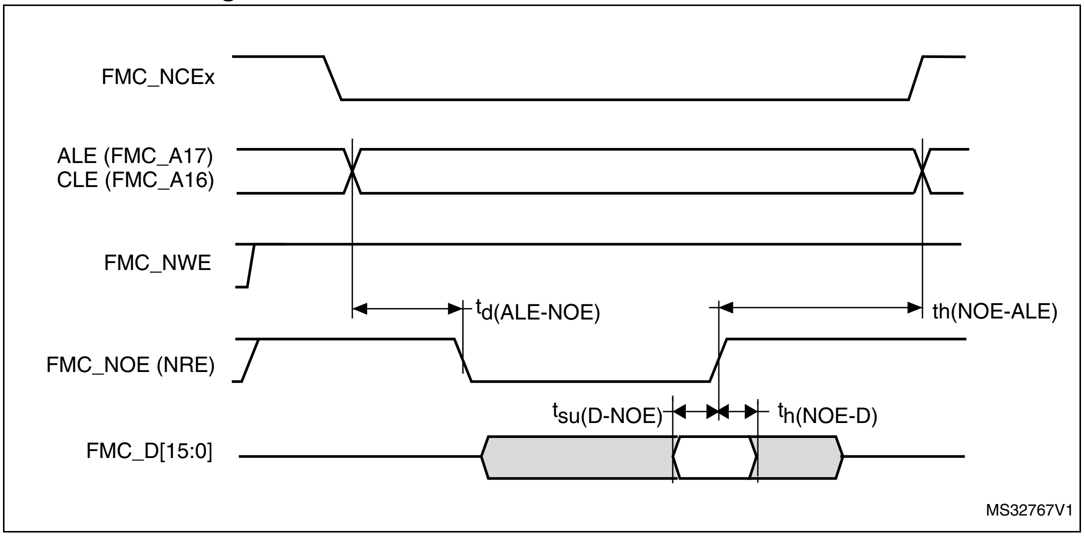


Figure 70. NAND controller waveforms for write access

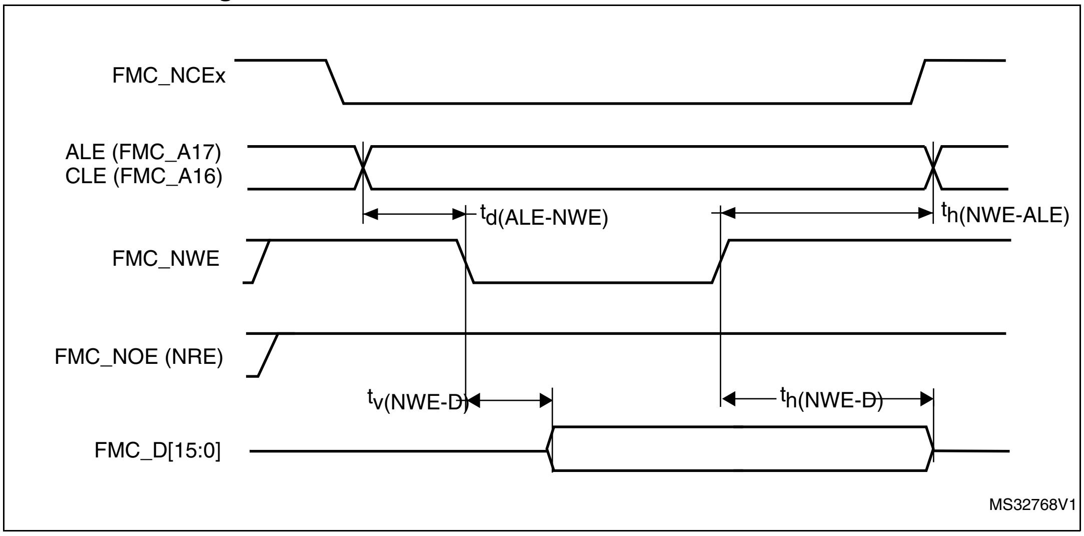
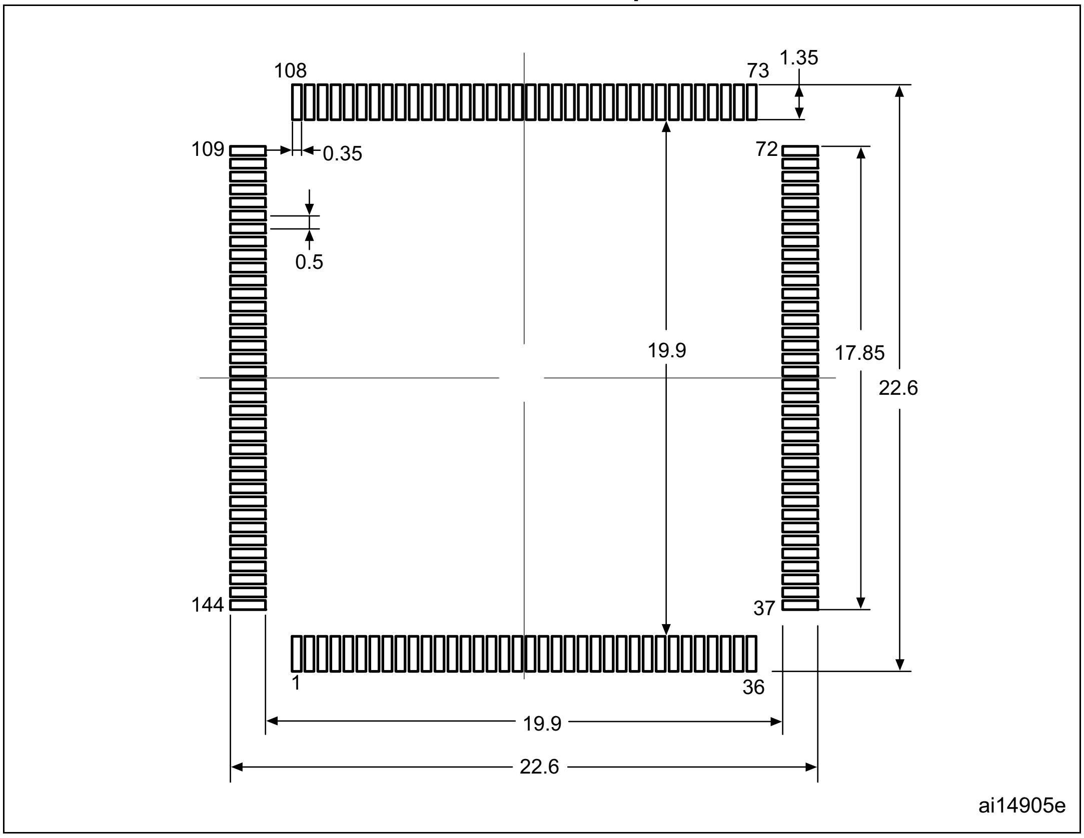


Figure 87. LQPF144- 144-pin,20 x 20 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

Table 116. UFBGA169 - 169-ball 7 x 7 mm 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
F	0.450	0.500	0.550	0.0177	0.0197	0.0217
ddd	-	-	0.100	-	-	0.0039
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 96. UFBGA169 - 169-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array recommended footprint

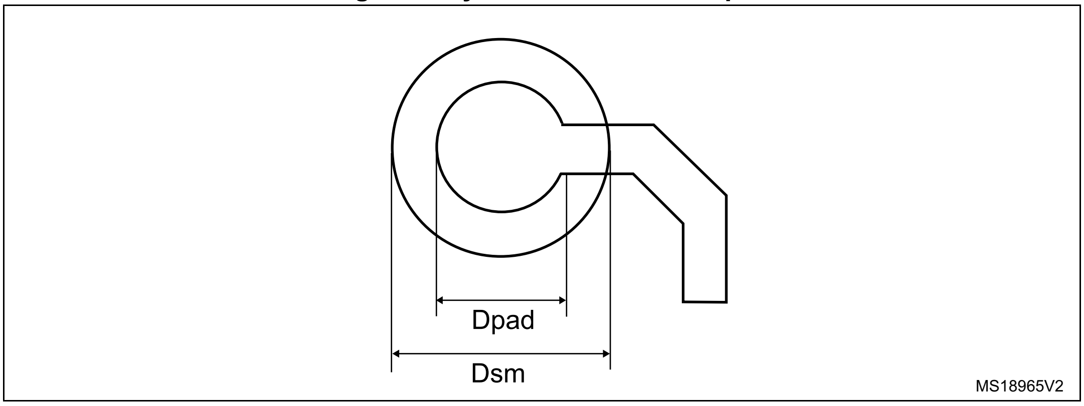


Table 117. UFBGA169 recommended PCB design rules (0.5 mm pitch BGA)

Dimension	Recommended values
Pitch	0.5
Dpad	0.27 mm
Dsm	0.35 mm typ. (depends on the soldermask registration tolerance)
Solder paste	0.27 mm aperture diameter.

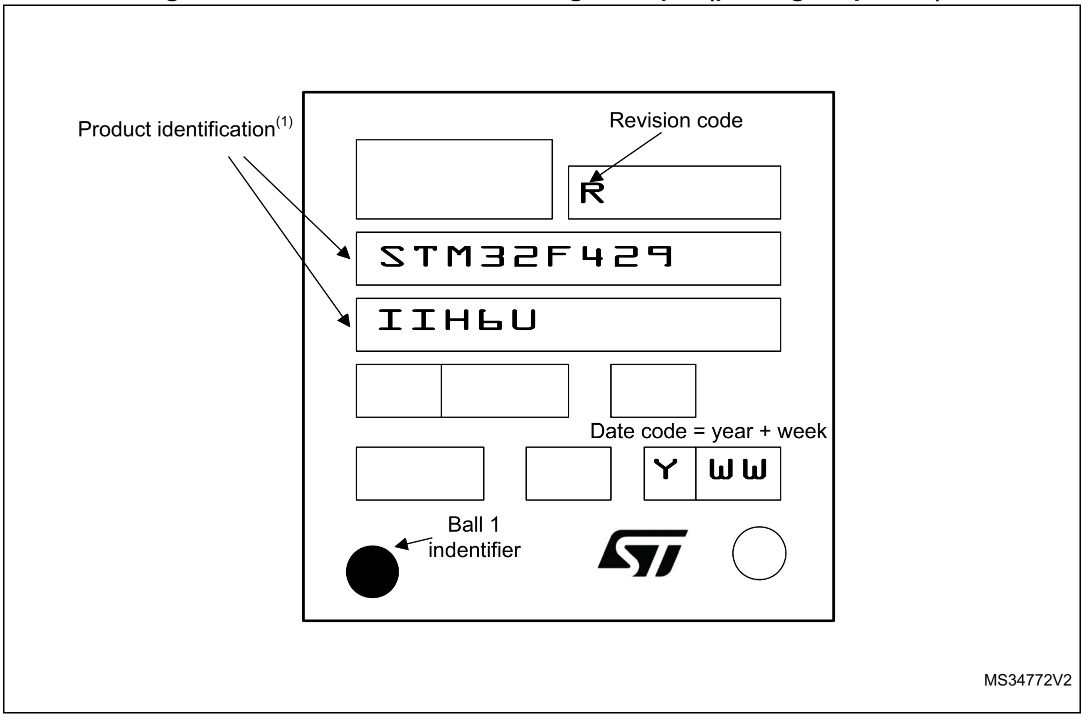
Note: *Non-solder mask defined (NSMD) pads are recommended.*
4 to 6 mils solder paste screen printing process.

Device marking for UFBGA176+25

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which depends assembly location, are not indicated below.

Figure 100. UFBGA176+25 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.